

CMNTVS12V

**SURFACE MOUNT
UNI-DIRECTIONAL
12 VOLT SILICON QUAD TVS ARRAY**


www.centralsemi.com
DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMNTVS12V is a 4-line TVS arrays in a space saving SOT-953 surface mount package. This device is designed to protect sensitive equipment against ESD damage.

MARKING CODE: CY
FEMTOmini™
**SOT-953 CASE**

- Device is *Halogen Free* by design

APPLICATIONS:

- PDAs
- Memory Card Ports
- Mobile Phones
- Instrumentation

FEATURES:

- Small, **FEMTOmini™** 1.0 x 0.8mm, SOT-953 Surface Mount Package
- Low Capacitance
- Low Leakage Current
- ESD Protection IEC 61000-4-2: Level 4 (8kV) HBM
- 4-Line Array

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Power Dissipation (8x20μs)	P_{PK}	18	W
ESD Voltage (Human Body Model - HBM)	V_{ESD}	8.0	kV
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	°C

SYMBOL**UNITS****ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$)**

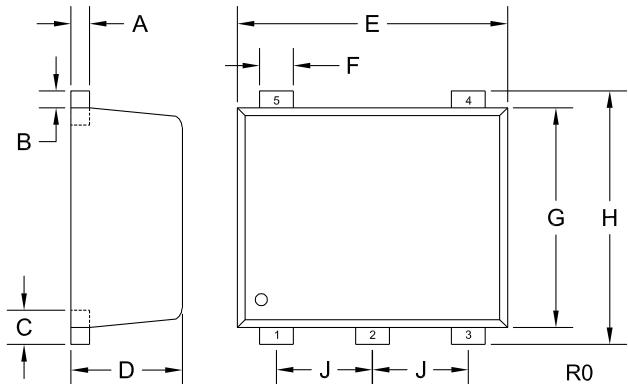
Breakdown Voltage V_{BR} @ 5.0mA			Maximum Leakage Current I_{RWM} @ V_{RWM}		Maximum Clamping Voltage V_C @ I_{PP}		Maximum Capacitance @ 0V Bias	Maximum Capacitance @ 3V Bias
MIN V	NOM V	MAX V	μA	V	V	A	pF	pF
11.4	12.0	12.7	0.5	9.0	18	1.0	10	6.0

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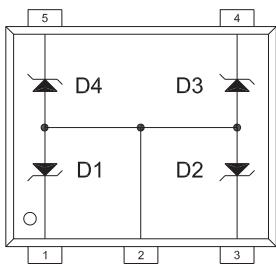
SOT-953 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.002	0.006	0.050	0.150
B	0.002	0.006	0.050	0.150
C	0.005	0.007	0.125	0.175
D	0.016	0.020	0.400	0.500
E	0.037	0.041	0.950	1.050
F	0.004	0.008	0.100	0.200
G	0.030	0.033	0.750	0.850
H	0.037	0.041	0.950	1.050
J	0.014		0.350	

SOT-953 (REV: R0)

PIN CONFIGURATION



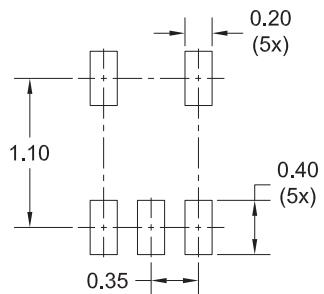
LEAD CODE:

- 1) Cathode D1
- 2) Anode D1, D2, D3, D4
- 3) Cathode D2
- 4) Cathode D3
- 5) Cathode D4

MARKING CODE: CY

SUGGESTED MOUNTING PADS

(Dimensions in mm)



R0

R3 (3-January 2012)

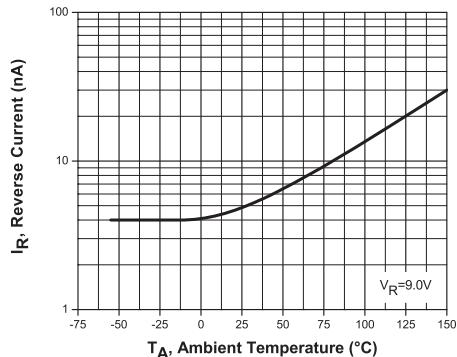
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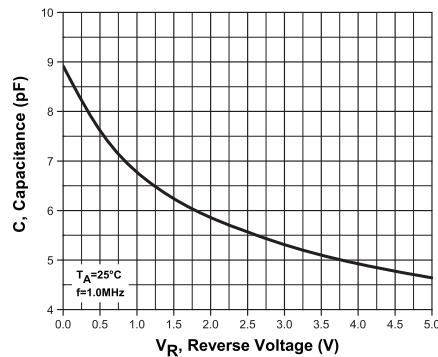


TYPICAL ELECTRICAL CHARACTERISTICS

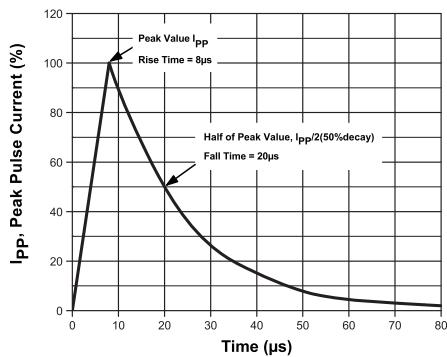
Leakage Current



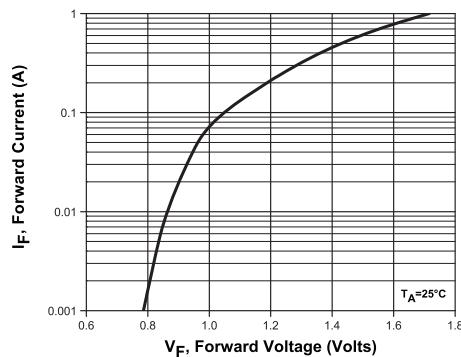
Capacitance



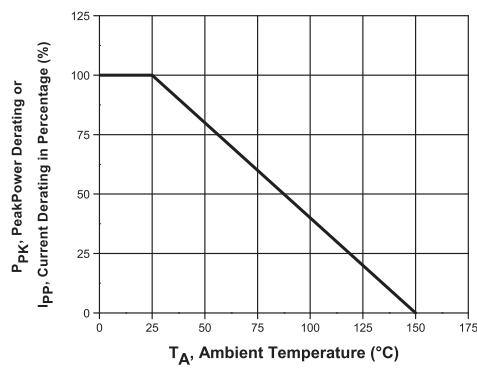
8 × 20 μ s Pulse Waveform



Forward Voltage



Normalized Power & Current Derating



R3 (3-January 2012)